



# STB6N52K3, STD6N52K3 STF6N52K3, STP6N52K3

N-channel 525 V, 1  $\Omega$  5 A, D<sup>2</sup>PAK, DPAK, TO-220FP, TO-220  
SuperMESH3™ Power MOSFET

## Features

Order codes	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>	P <sub>w</sub>
STB6N52K3	525 V	< 1.2 $\Omega$	5 A	70 W
STD6N52K3			5 A <sup>(1)</sup>	25 W
STF6N52K3			5 A	70 W
STP6N52K3			5 A	70 W

1. Limited by package

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

## Application

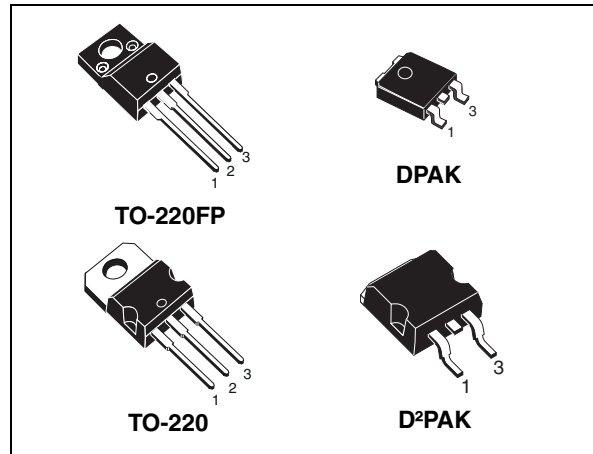
Switching applications

## Description

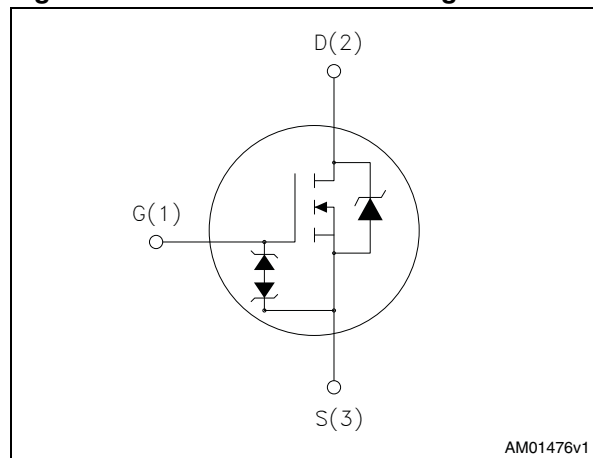
These devices are made using the SuperMESH3™ Power MOSFET technology that is obtained via improvements applied to STMicroelectronics' SuperMESH™ technology combined with a new optimized vertical structure. The resulting product has an extremely low on resistance, superior dynamic performance and high avalanche capability, making it especially suitable for the most demanding applications.

**Table 1. Device summary**

Order codes	Marking	Package	Packaging
STB6N52K3	6N52K3	D <sup>2</sup> PAK	Tape and reel
STD6N52K3		DPAK	
STF6N52K3		TO-220FP	Tube
STP6N52K3		TO-220	



**Figure 1. Internal schematic diagram**



AM01476v1

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value				Unit
		TO-220	D <sup>2</sup> PAK	DPAK	TO-220FP	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	525				V
$V_{GS}$	Gate- source voltage	$\pm 30$				V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5		5 <sup>(1)</sup>		A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3		3 <sup>(1)</sup>		A
$I_{DM}^{(2)}$	Drain current (pulsed)	20		20 <sup>(1)</sup>		A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70		25		W
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	2.5				A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{V}$ )	110				mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	12				V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ }^\circ\text{C}$ )					2500 V
$T_{stg}$	Storage temperature	- 55 to 150				$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150				$^\circ\text{C}$

- Limited by package
- Pulse width limited by safe operating area
- $I_{SD} \leq 5\text{ A}$ ,  $di/dt = 400\text{ V}$ ,  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		TO-220	D <sup>2</sup> PAK	DPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.79			5	$^\circ\text{C/W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max		30	50		$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5			62.5	$^\circ\text{C/W}$
$T_l$	Maximum lead temperature for soldering purpose	300			300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	525			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$		1	1.2	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	670	-	pF
$C_{oss}$	Output capacitance			54		pF
$C_{rss}$	Reverse transfer capacitance			10		pF
$C_{oss\ eq}^{(1)}$	Equivalent output capacitance			TBD		pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 420\text{ V}$ , $I_D = 5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 20</a> )	-	26	-	nC
$Q_{gs}$	Gate-source charge			4		nC
$Q_{gd}$	Gate-drain charge			15		nC

1.  $C_{oss\ eq}^{(1)}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 260\text{ V}$ , $I_D = 2.5\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19</a> )	-	10	-	ns
$t_r$	Rise time			11		ns
$t_{d(off)}$	Turn-off-delay time			31		ns
$t_f$	Fall time			18		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5 \text{ A}, V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 24</a> )	-	206		ns
$Q_{rr}$	Reverse recovery charge			1.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			14		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 24</a> )	-	233		ns
$Q_{rr}$	Reverse recovery charge			1.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			15		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

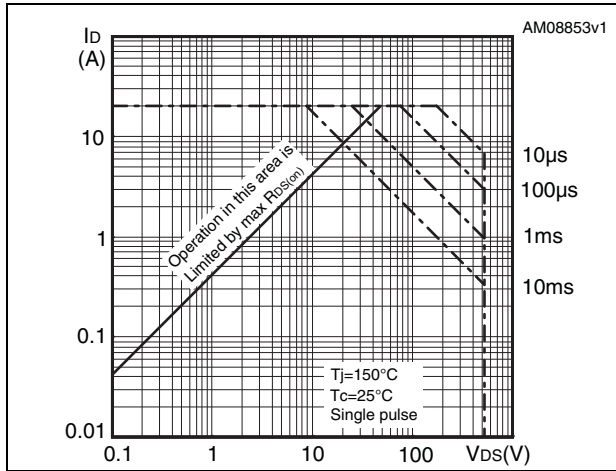
**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{gs} = \pm 1 \text{ mA}$ (open drain)	30			V

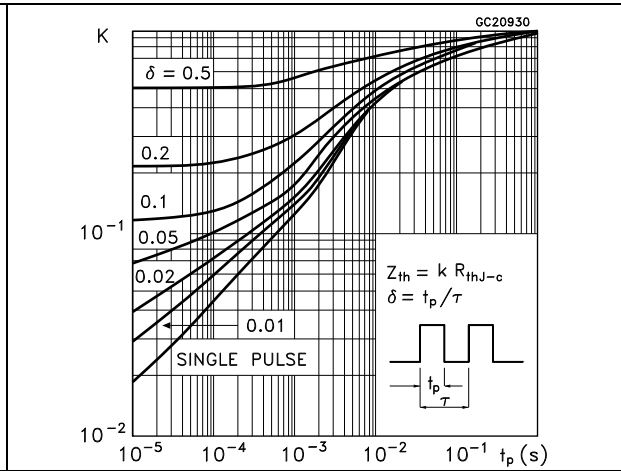
The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

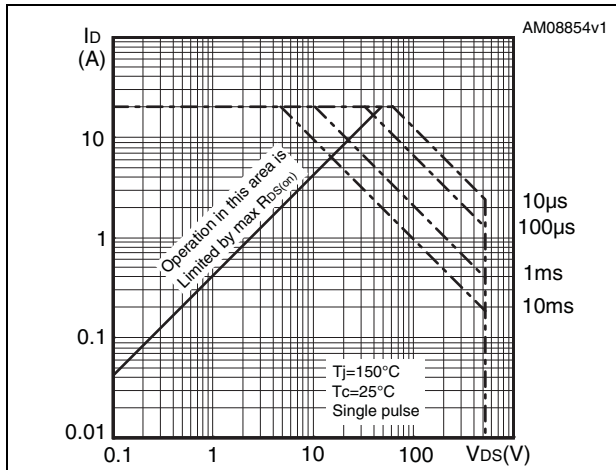
**Figure 2. Safe operating area for TO-220, D<sup>2</sup>PAK**



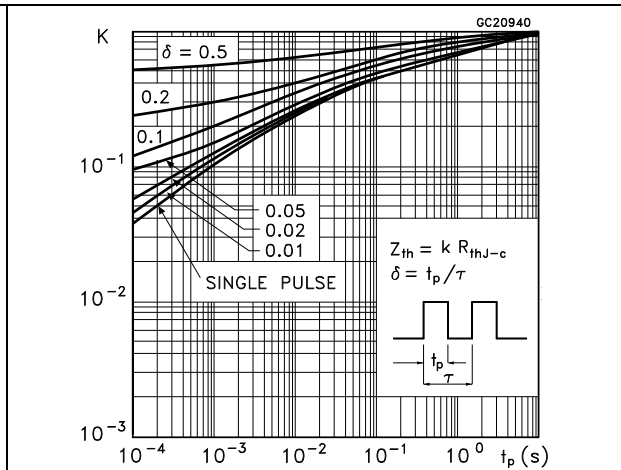
**Figure 3. Thermal impedance for TO-220, D<sup>2</sup>PAK**



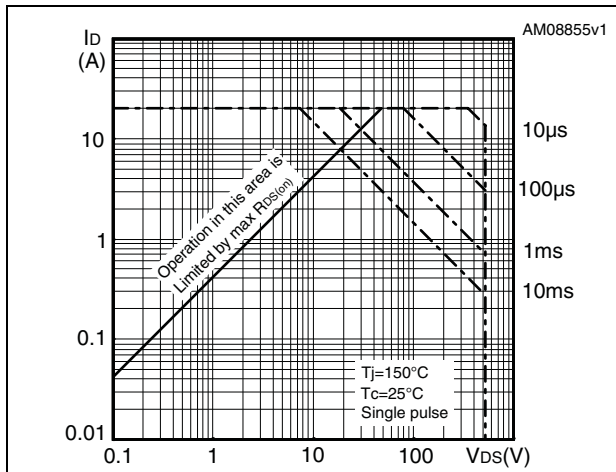
**Figure 4. Safe operating area for TO-220FP**



**Figure 5. Thermal impedance for TO-220FP**



**Figure 6. Safe operating area for DPAK**



**Figure 7. Thermal impedance for DPAK**

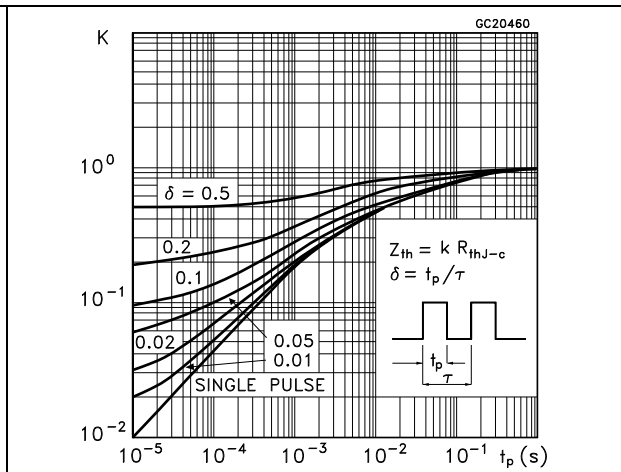


Figure 8. Output characteristics

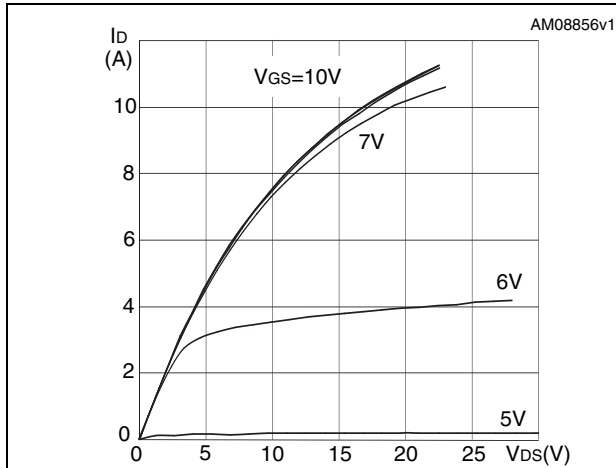


Figure 9. Transfer characteristics

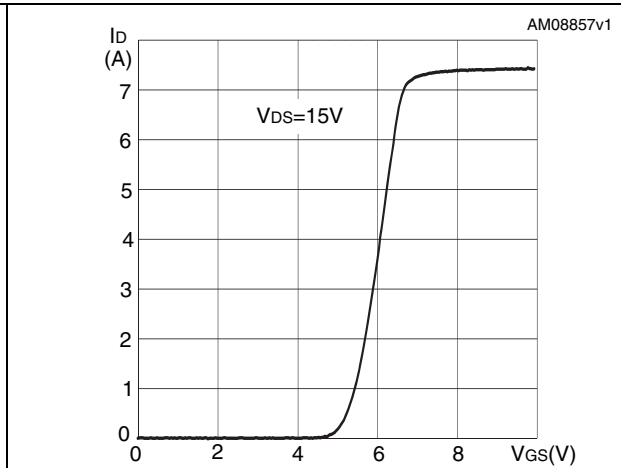


Figure 10. Gate charge vs gate-source voltage

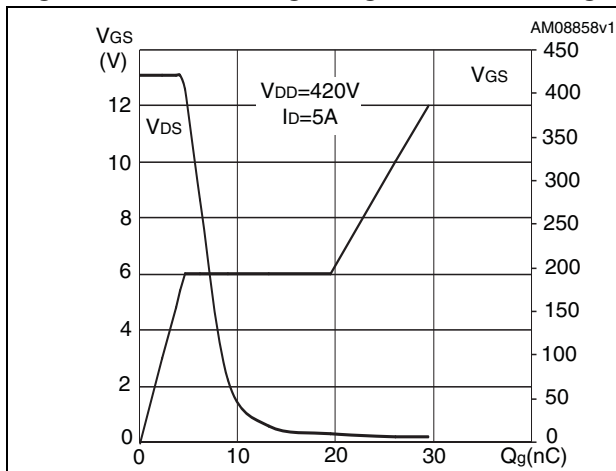


Figure 11. Static drain-source on resistance

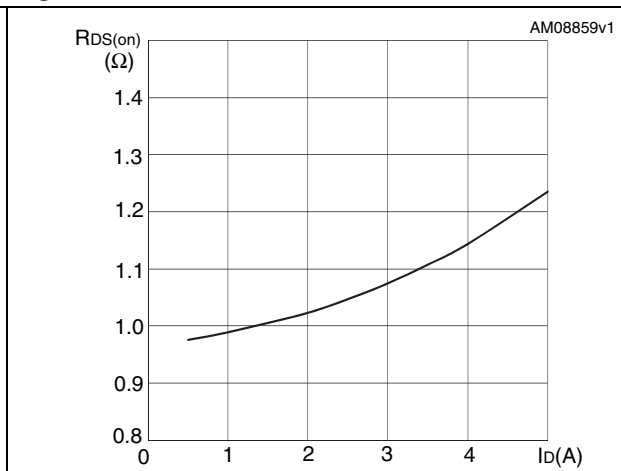


Figure 12. Capacitance variations

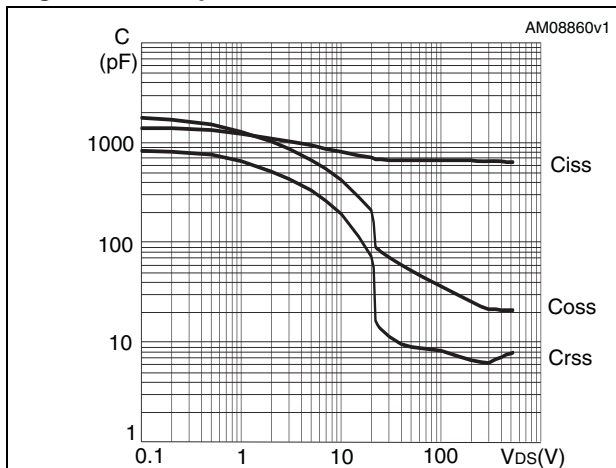


Figure 13. Output capacitance stored energy

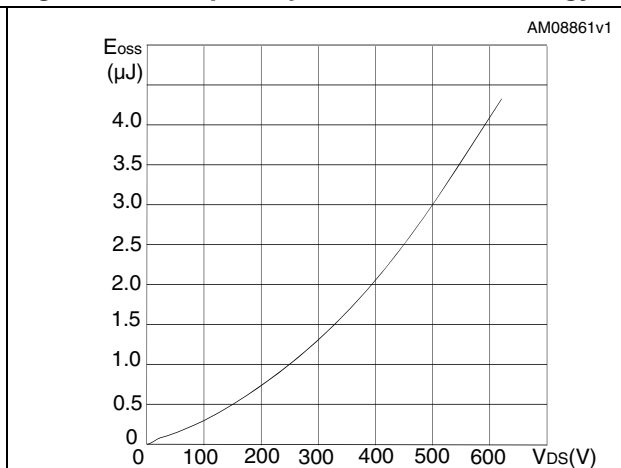


Figure 14. Normalized gate threshold voltage vs temperature

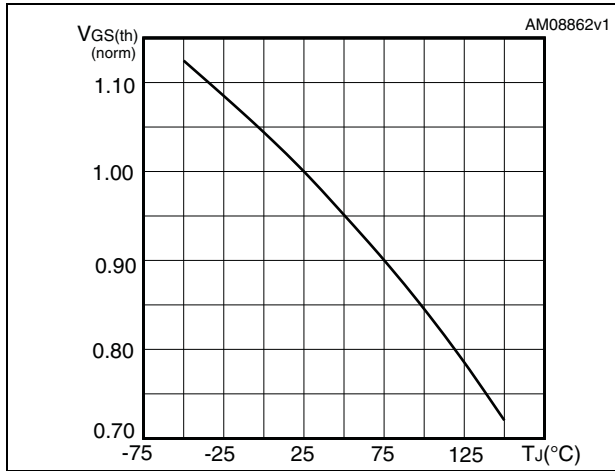


Figure 15. Normalized on resistance vs temperature

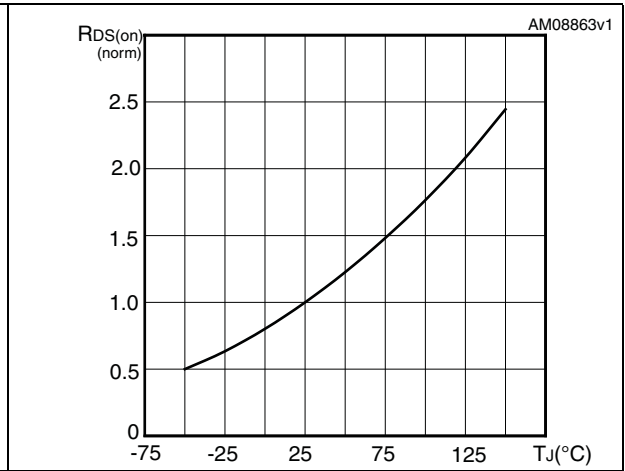


Figure 16. Source-drain diode forward characteristics

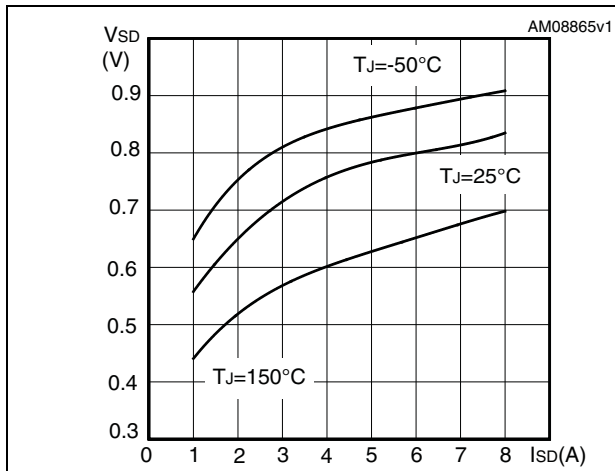


Figure 17. Normalized B<sub>VDSS</sub> vs temperature

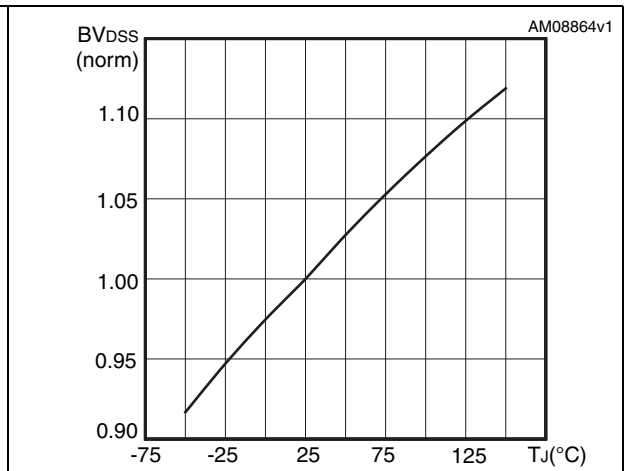
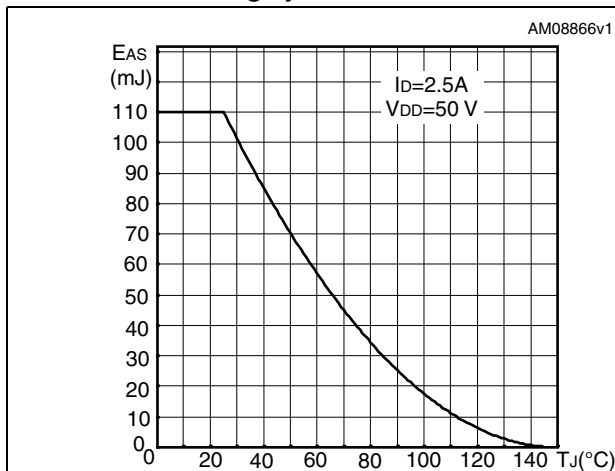


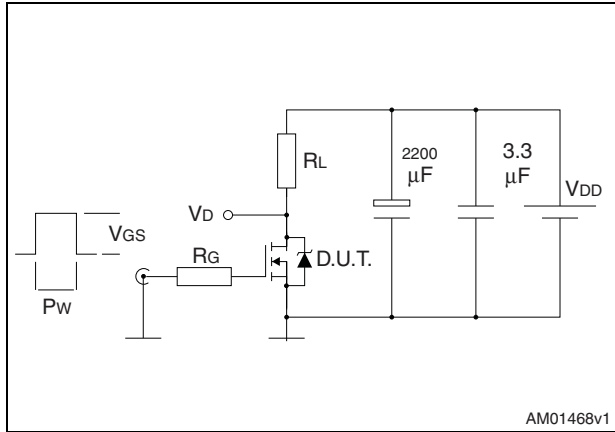
Figure 18. Maximum avalanche energy vs starting Tj





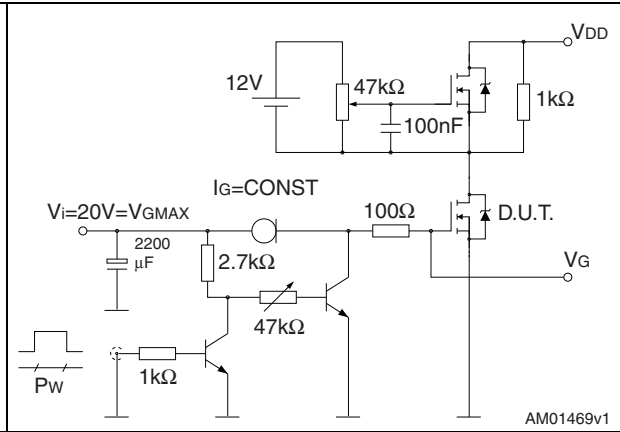
### 3 Test circuits

**Figure 19. Switching times test circuit for resistive load**



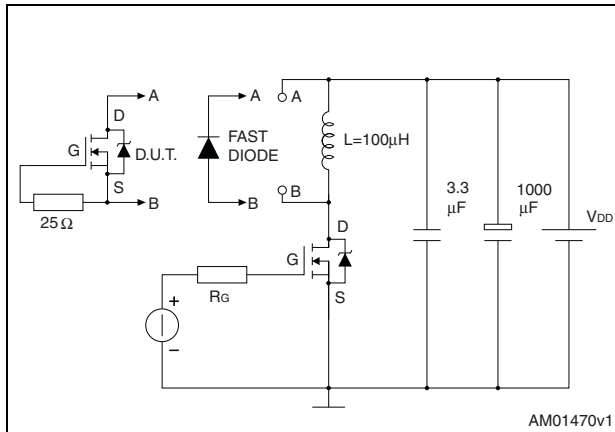
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**Figure 20. Gate charge test circuit**



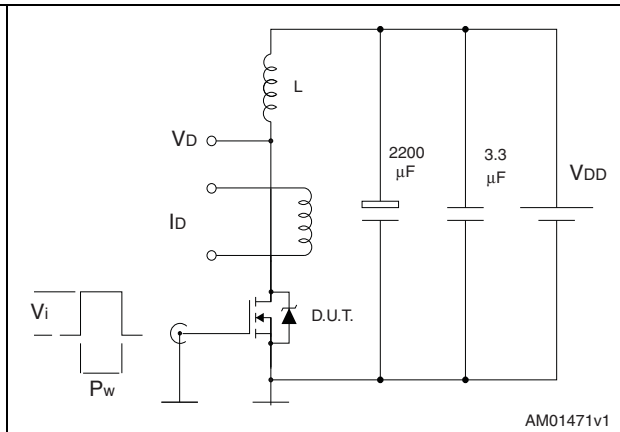
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**Figure 21. Test circuit for inductive load switching and diode recovery times**



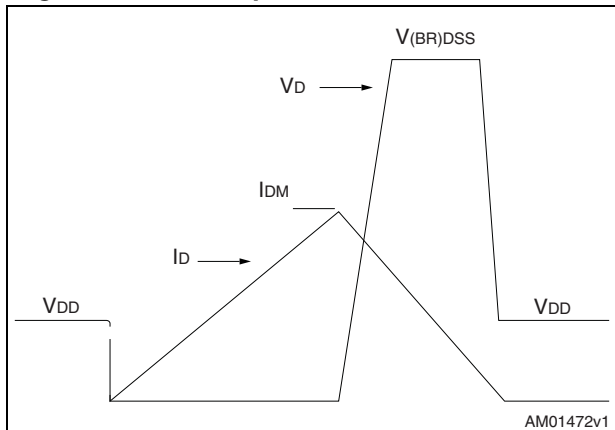
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**Figure 22. Unclamped Inductive load test circuit**



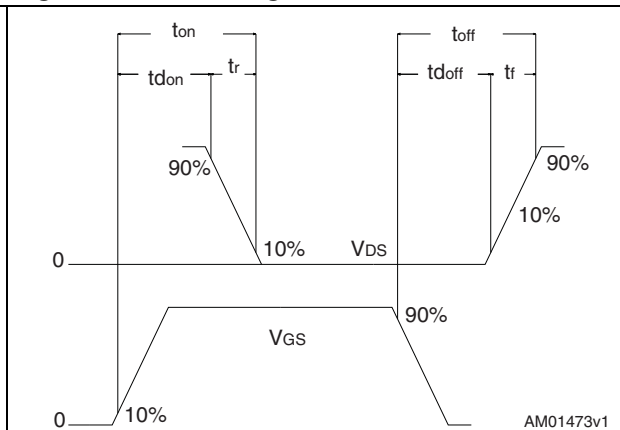
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**Figure 23. Unclamped inductive waveform**



AM01472v1

**Figure 24. Switching time waveform**



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 9. D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D<sup>2</sup>PAK (TO-263) drawing

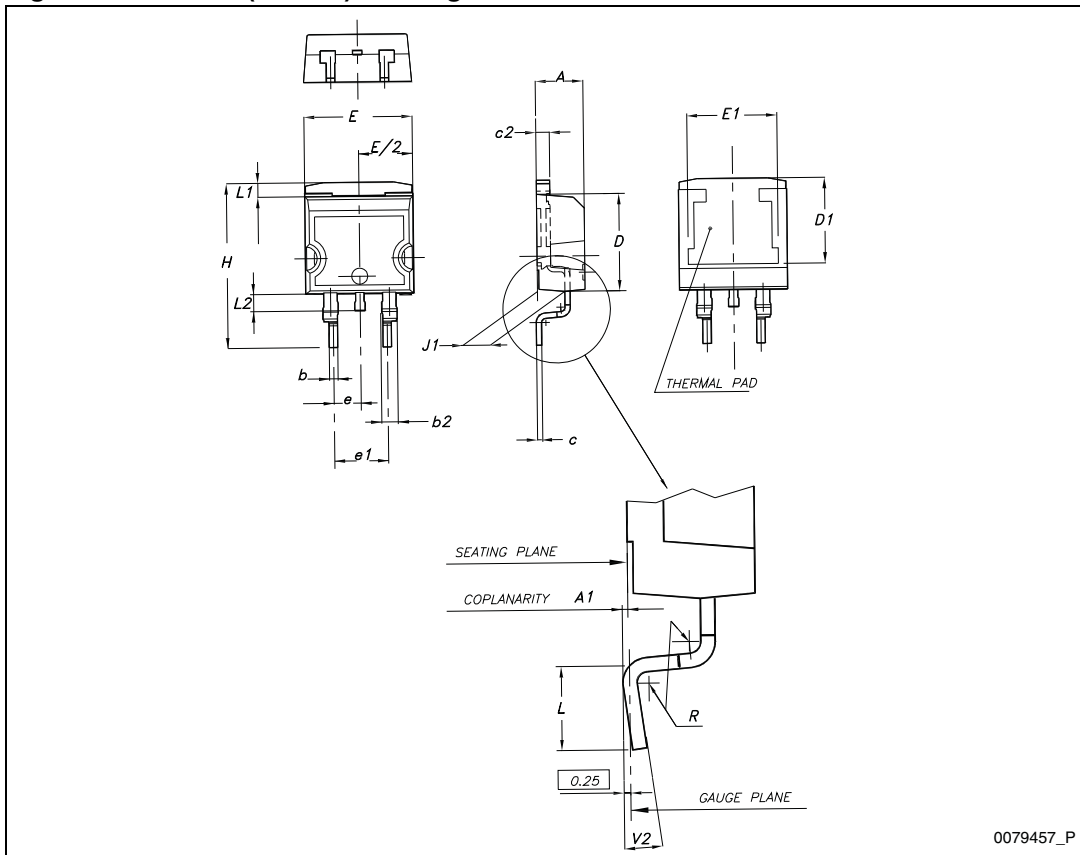


Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 26. DPAK (TO-252) drawing

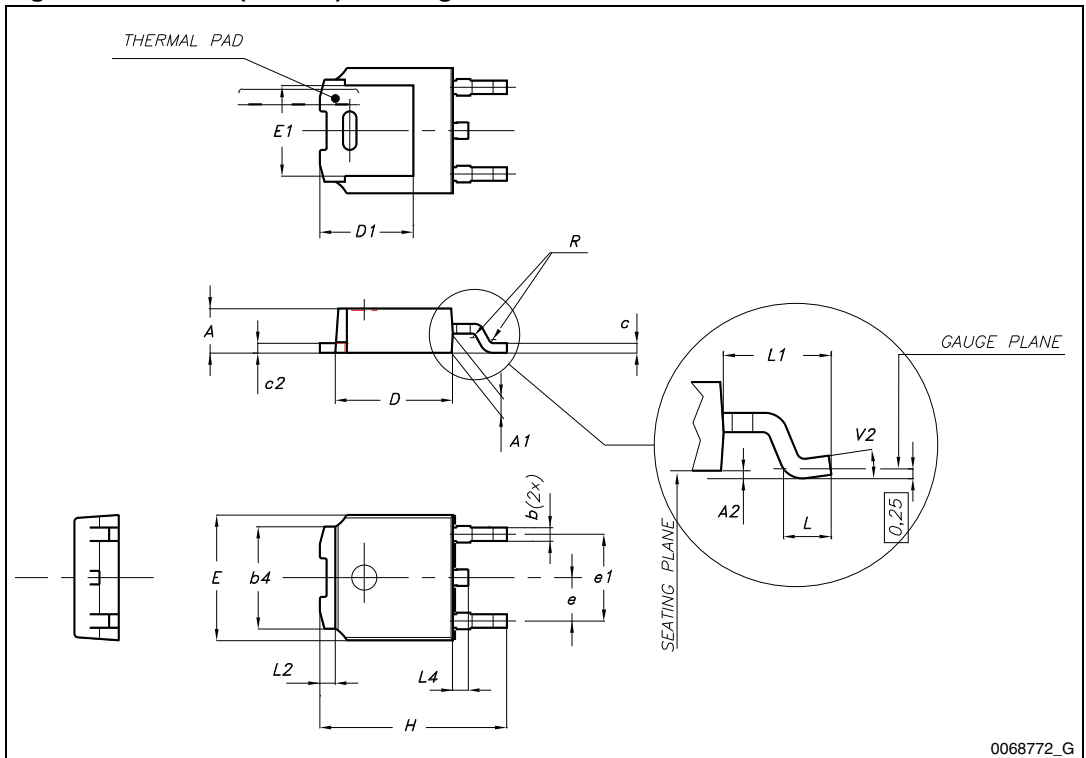
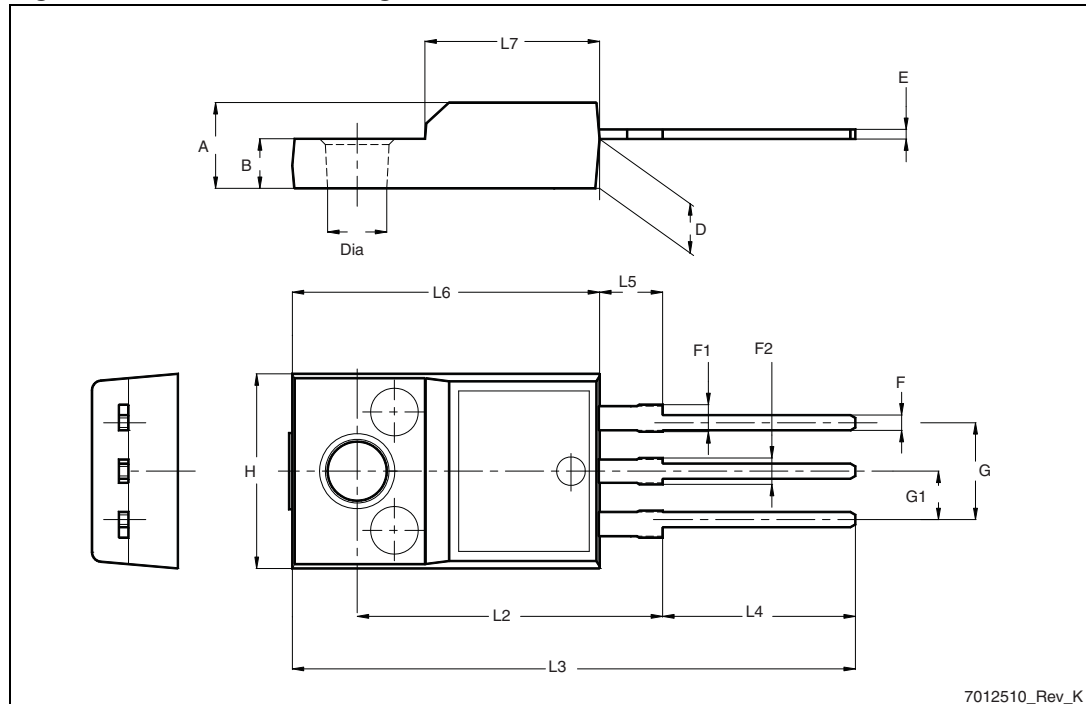


Table 11. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 27. TO-220FP drawing



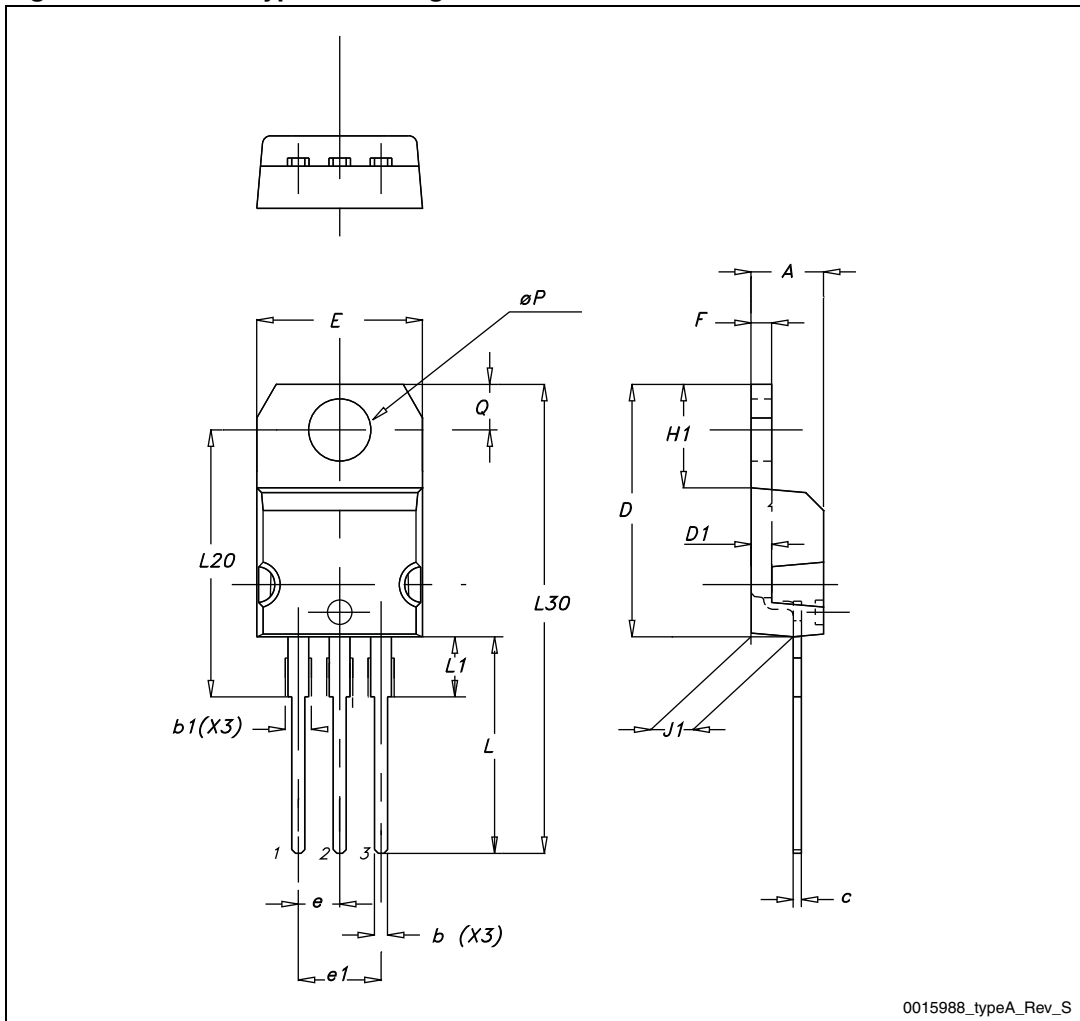
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Table 12. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



Figure 28. TO-220 type A drawing

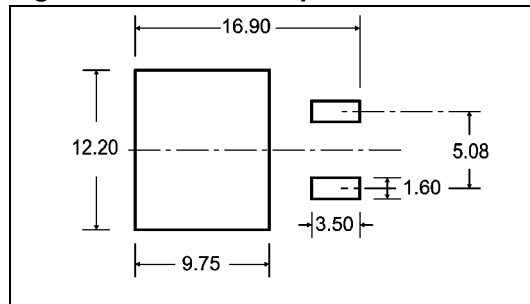


## 5 Packaging mechanical data

**Table 13. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

**Figure 29. D<sup>2</sup>PAK footprint<sup>(a)</sup>**

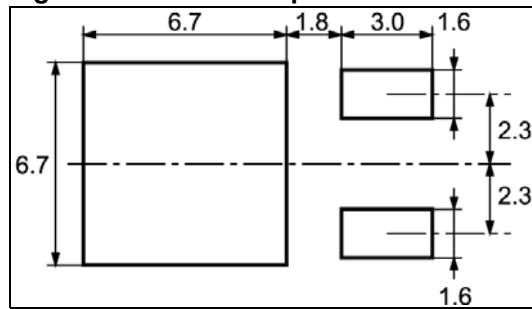


a. All dimension are in millimeters

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	<b>Base qty</b>		2500
P1	7.9	8.1	<b>Bulk qty</b>		2500
P2	1.9	2.1			
R	40				
W	15.7	16.3			

Figure 30. DPAK footprint<sup>(b)</sup>



b. All dimension are in millimeters

Figure 31. Tape

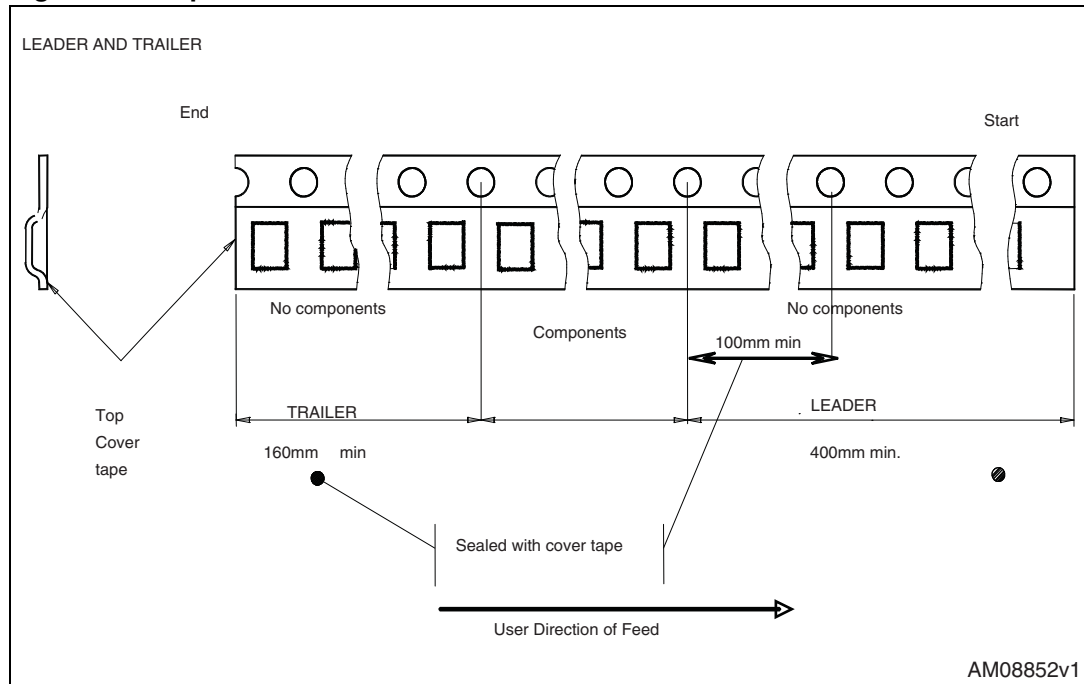
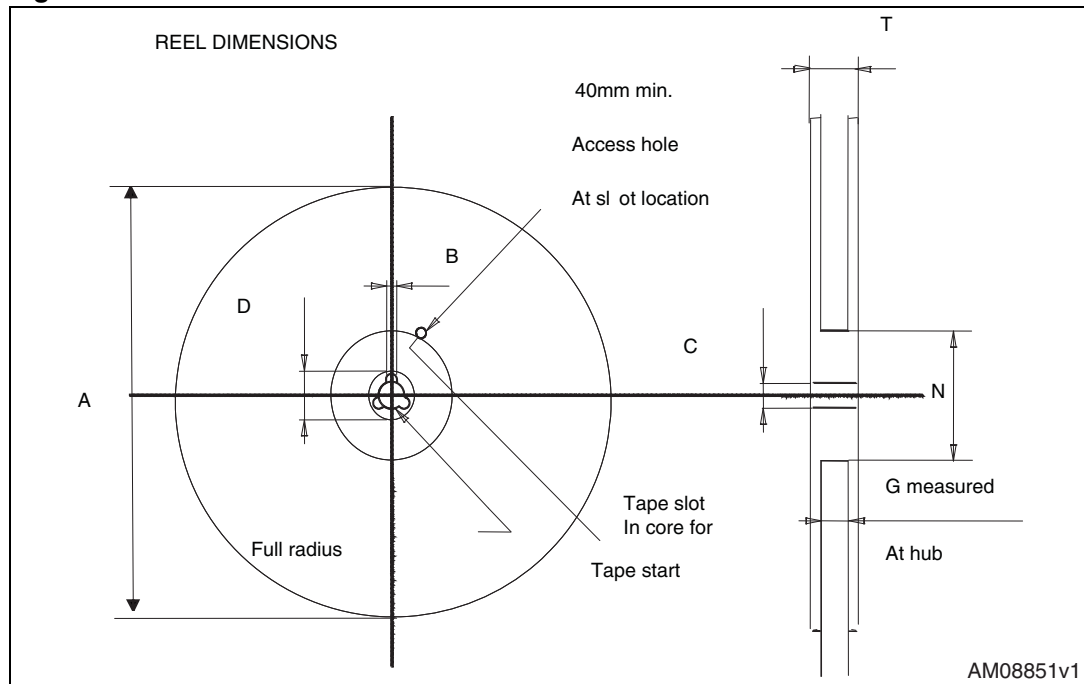


Figure 32. Reel



## 6 Revision history

**Table 15. Document revision history**

Date	Revision	Changes
03-Sep-2008	1	Initial release.
21-Feb-2011	2	– Added new package, mechanical data: D <sup>2</sup> PAK; – Added new package, mechanical data: TO-220; – Document status promoted from preliminary data to datasheet.

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